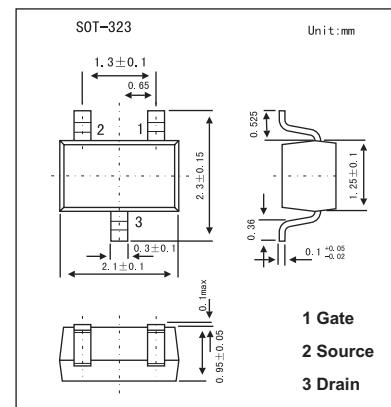
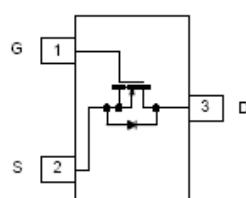


N-Channel 30-V (D-S) MOSFET

KI1302DL

■ Features

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■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	5 secs	Steady State	Unit
Drain-source voltage	V _{DS}		30	V
Gate-source voltage	V _{GSS}		±20	V
Continuous drain current (T _J = 150°C) TA=25°C TA=70°C	I _D	0.64 0.51	0.60 0.48	A
Pulsed drain current	I _{DM}		1.5	A
Continuous source current (diode conduction) *	I _S	0.26	0.23	A
Power dissipation * TA=25°C TA=70°C	P _D	0.31 0.20	0.28 0.18	W
Operating junction and storage temperature range	T _j , T _{stg}		-55 to +150	°C

* Surface Mounted on 1" X 1" FR4 Board.

■ Thermal Resistance Ratings Ta = 25°C

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient* t ≤ 5 sec	R _{thJA}	355	400	°C/W
Steady State		380	450	
Maximum Junction-to-Foot (Drain)	R _{thJF}	285	340	

* Surface Mounted on 1" X 1" FR4 Board.

KI1302DL■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Gate threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	1			V
Gate-body leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 24 \text{ V}$, $V_{GS} = 0 \text{ V}$		1		μA
		$V_{DS} = 24 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 70^\circ\text{C}$		5		
On-state drain current	$I_{D(\text{on})}$	$V_{DS} = 5 \text{ V}$, $V_{GS} = 10 \text{ V}$	1.5			A
Drain-source on-state resistance	$r_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.6 \text{ A}$		0.410	0.480	Ω
		$V_{GS} = 4.5 \text{ V}$, $I_D = 0.2 \text{ A}$		0.600	0.700	
Forward transconductance	g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 0.6 \text{ A}$		0.75		S
Diode forward voltage	V_{SD}	$I_S = 0.23 \text{ A}$, $V_{GS} = 0 \text{ V}$		0.8	1.2	V
Total gate charge *	Q_g	$V_{DS} = 15 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 0.6 \text{ A}$		0.86	1.4	nC
Gate-source charge *	Q_{gs}			0.24		
Gate-drain charge *	Q_{gd}			0.08		
Turn-on time	$t_{d(on)}$	$V_{DD} = 15 \text{ V}$, $R_L = 30 \Omega$, $I_D = 0.5 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_G = 6 \Omega$		5	10	ns
	t_r			8	15	
Turn-off time	$t_{d(off)}$			8	15	
	t_f			7	15	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 0.23 \text{ A}$, $d/I/dt = 100 \text{ A}/\mu\text{s}$		15	30	

* Pulse test: $PW \leq 300 \mu\text{s}$ duty cycle $\leq 2\%$.

■ Marking

Marking	KA
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